

Substitution for form 1449A/PTO
**INFORMATION DISCLOSURE
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PTO/USDOA(10-01)
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Complete if Known	
Application Number	10/789,044
Filing Date	February 27, 2004
First Named Inventor	Ahn, Kie
Group Art Unit	2829
Examiner Name	Menz, Douglas
Attorney Docket No: 1303.070US2	

Sheet 1 of 4

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* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached

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	Examiner Name	Menz, Douglas
Sheet 2 of 4	Attorney Docket No: 1303.070US2	

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Examiner Name	Menz, Douglas

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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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Substitute Disclosure Statement Form (PTO-1448)

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Group Art Unit	Unknown
Examiner Name	Unknown

Sheet 1 of 6

Attorney Docket No: 1303.070US2

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	Group Art Unit	Unknown
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First Named Inventor	Ahn, Kie
Group Art Unit	Unknown
Examiner Name	Unknown

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First Named Inventor	Ahn, Kie
Group Art Unit	Unknown
Examiner Name	Unknown

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	First Named Inventor	Ahn, Kie
	Group Art Unit	Unknown
	Examiner Name	Unknown
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